

MDP12N50B / MDF12N50B

N-Channel MOSFET 500V, 11.5A, 0.65Ω

General Description

The MDP/F12N50B uses advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

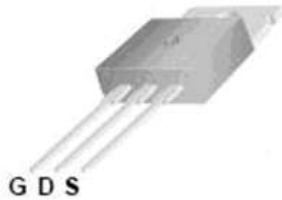
MDP/F12N50B is suitable device for SMPS, high Speed switching and general purpose applications.

Features

- $V_{DS} = 500V$
- $I_D = 11.5A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 0.65\Omega$ @ $V_{GS} = 10V$

Applications

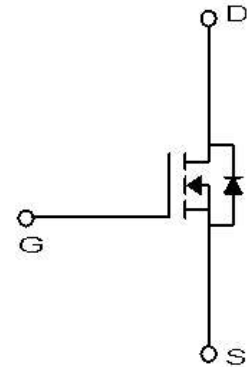
- Power Supply
- PFC
- Ballast



TO-220
MDP Series



TO-220F
MDF Series



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	MDP12N50B	MDF12N50B	Unit
Drain-Source Voltage		V_{DSS}	500		V
Gate-Source Voltage		V_{GSS}	±30		V
Continuous Drain Current	$T_C=25^\circ C$	I_D	11.5	11.5*	A
	$T_C=100^\circ C$		7.0	7.0*	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	46	46*	A
Power Dissipation	$T_C=25^\circ C$	P_D	165	42	W
	Derate above 25 °C		1.33	0.32	W/°C
Repetitive Avalanche Energy ⁽¹⁾		E_{AR}	16.5		mJ
Peak Diode Recovery dv/dt ⁽³⁾		dv/dt	4.5		V/ns
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	460		mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150		°C

※ Id limited by maximum junction temperature

Thermal Characteristics

Characteristics	Symbol	MDP12N50B	MDF12N50B	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	62.5	62.5	°C/W
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	0.75	3.0	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDP12N50BTH	-55~150°C	TO-220	Tube	Halogen Free
MDF12N50BTH	-55~150°C	TO-220F	Tube	Halogen Free

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	500	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 500V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 5.75A	-	0.55	0.65	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30V, I _D = 5.75A	-	15	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DS} = 400V, I _D = 11.5A, V _{GS} = 10V ⁽³⁾	-	19.3	-	nC
Gate-Source Charge	Q _{gs}		-	4.6	-	
Gate-Drain Charge	Q _{gd}		-	6.1	-	
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	1034	-	pF
Reverse Transfer Capacitance	C _{rss}		-	5.1	-	
Output Capacitance	C _{oss}		-	126	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 250V, I _D =11.5A, R _G = 25Ω ⁽³⁾	-	16	-	ns
Rise Time	t _r		-	35	-	
Turn-Off Delay Time	t _{d(off)}		-	31	-	
Fall Time	t _f		-	40	-	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I _S		-	11.5	-	A
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 11.5A, V _{GS} = 0V	-	-	1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 11.5A, di/dt = 100A/μs	-	310	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	2.6	-	μC

Note :

- Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
- Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ C$.
- $I_{SD} \leq 11.5A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ C$
- $L = 6.3mH$, $I_{AS} = 11.5A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ C$

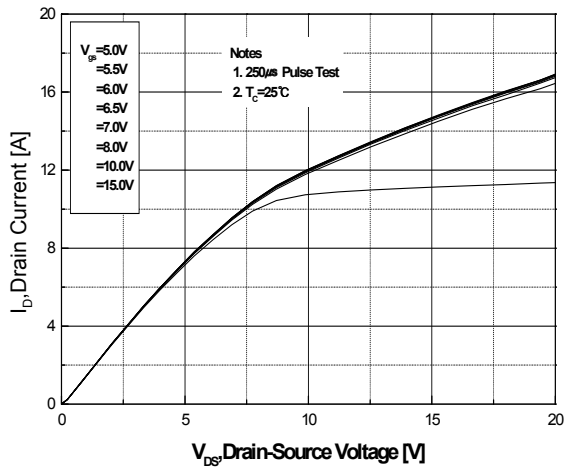


Fig.1 On-Region Characteristics

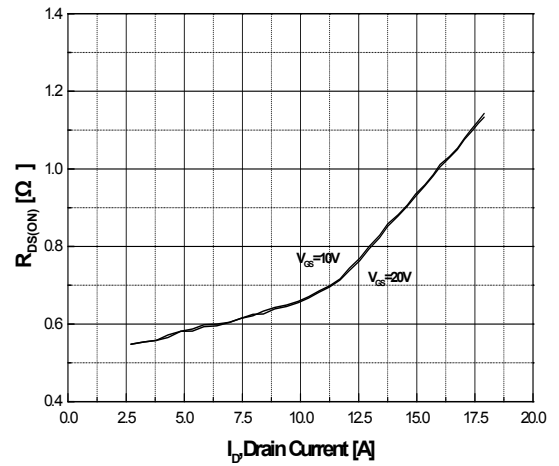


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

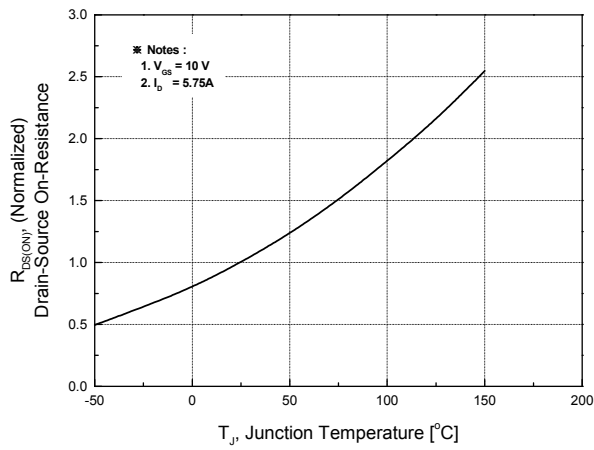


Fig.3 On-Resistance Variation with Temperature

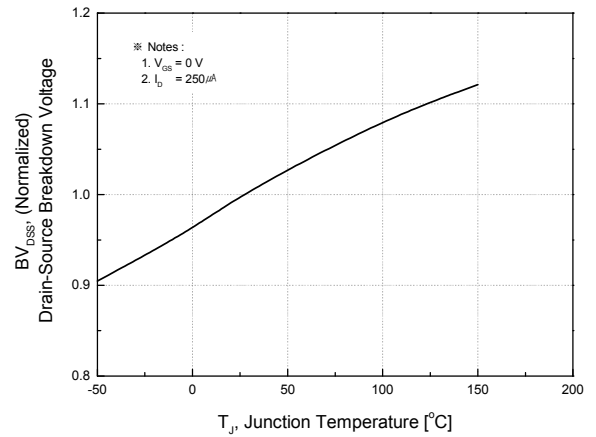


Fig.4 Breakdown Voltage Variation vs. Temperature

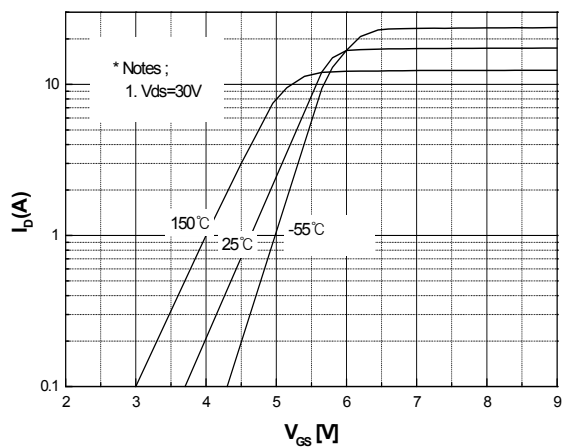


Fig.5 Transfer Characteristics

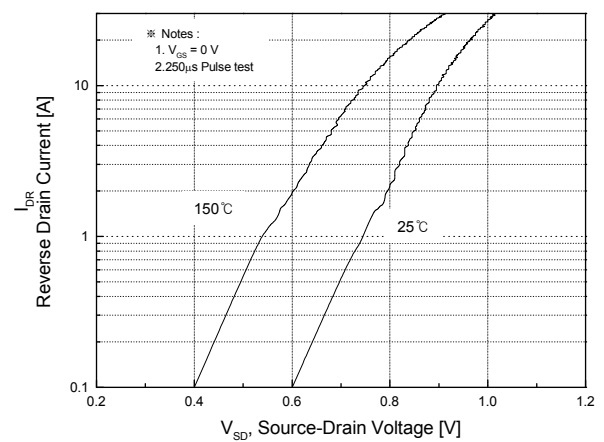


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

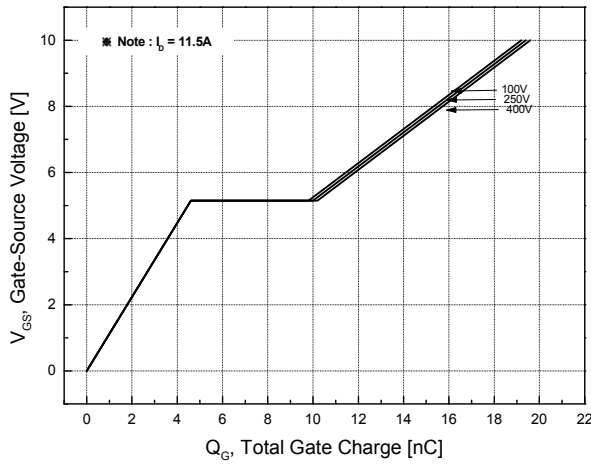


Fig.7 Gate Charge Characteristics

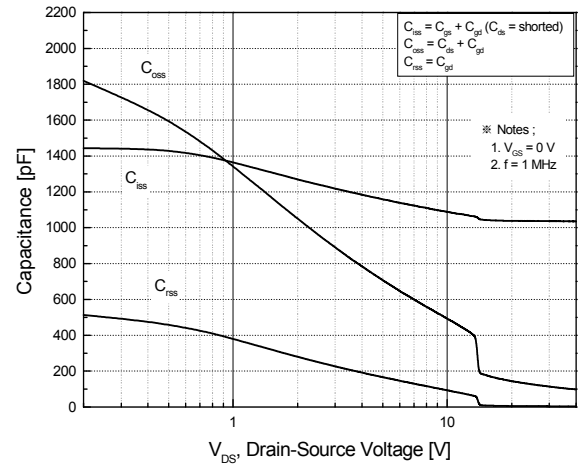


Fig.8 Capacitance Characteristics

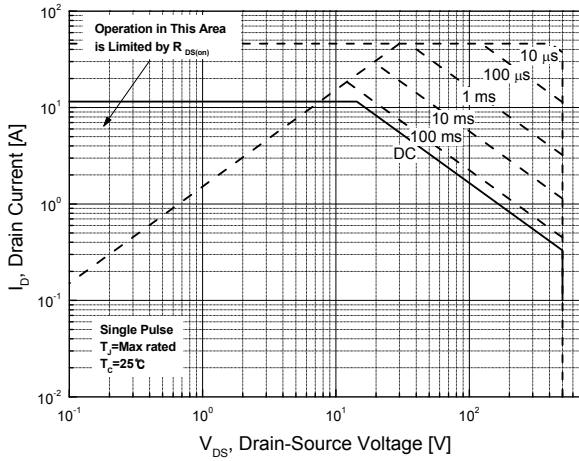
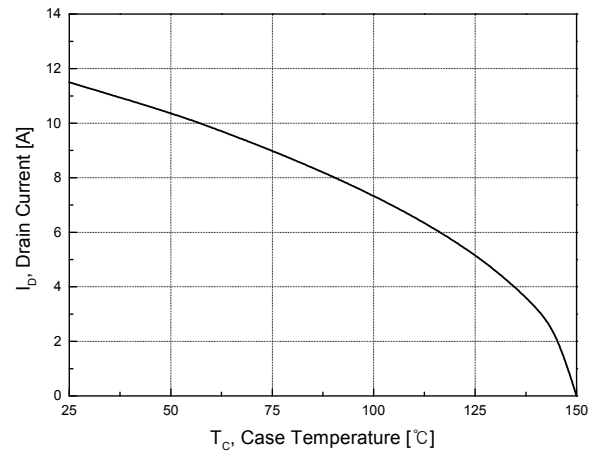
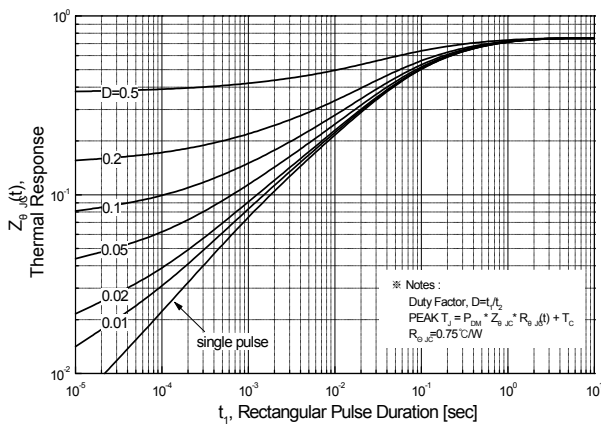
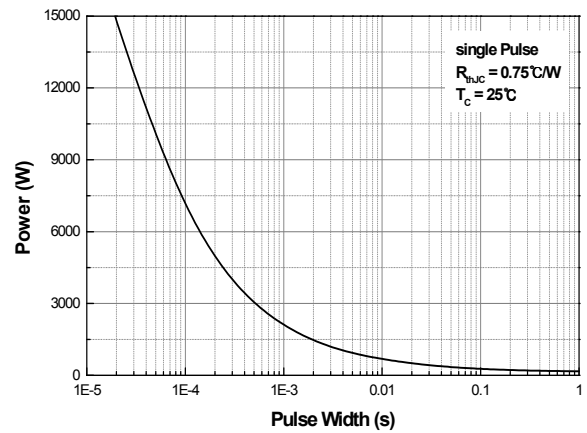
Fig.9 Maximum Safe Operating Area
MDP12N50B (TO-220)

Fig.10 Maximum Drain Current vs. Case Temperature

Fig.11 Transient Thermal Response Curve
MDP12N50B (TO-220)Fig.12 Single Pulse Maximum Power
Dissipation – MDP12N50B (TO-220)

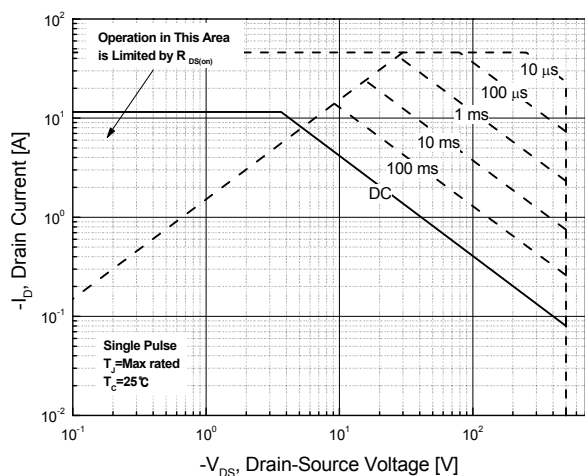


Fig.13 Maximum Safe Operating Area
MDF12N50B (TO-220F)

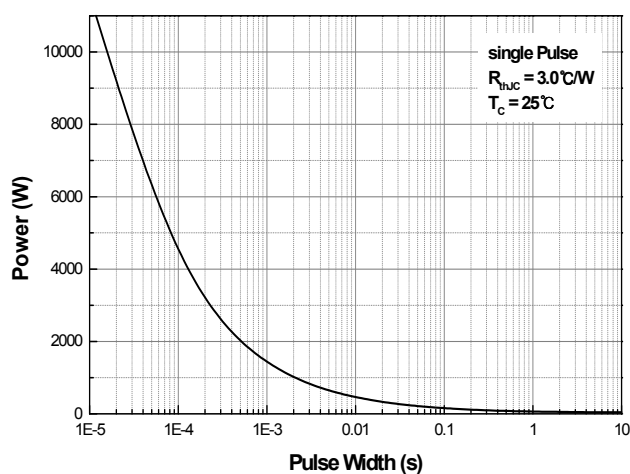


Fig.14 Single Pulse Maximum Power
Dissipation – MDF12N50B (TO-220F)

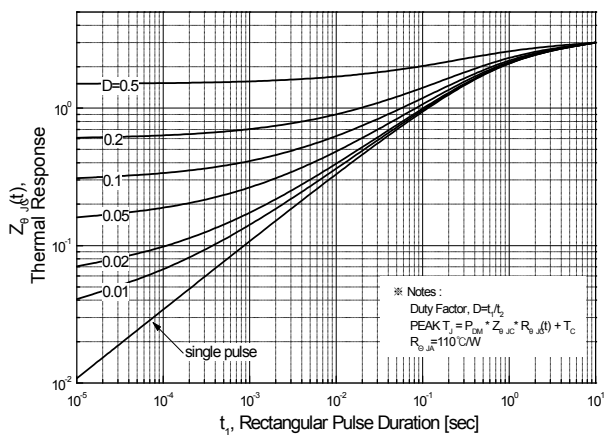
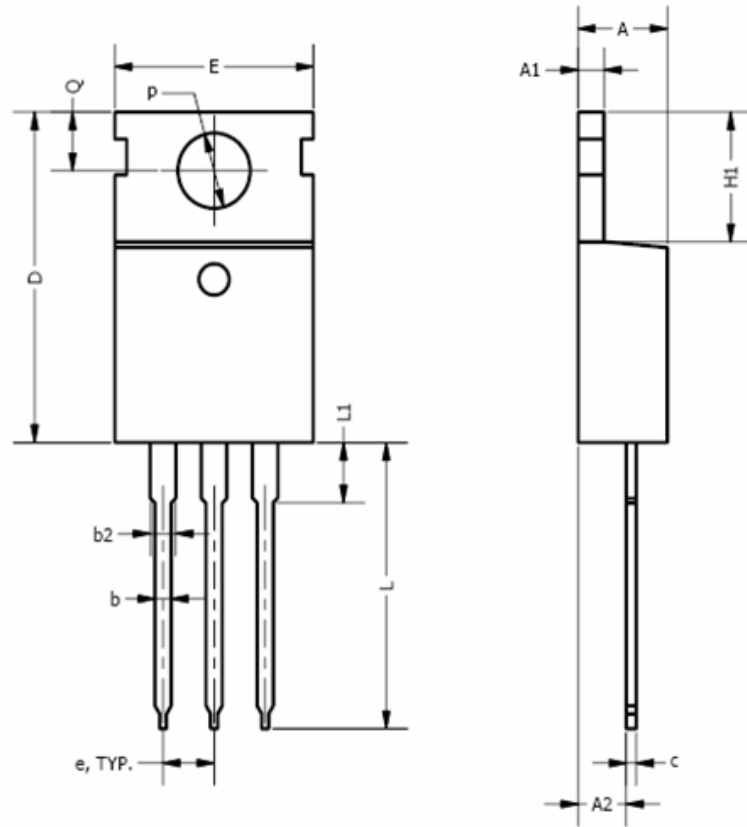


Fig.15 Transient Thermal Response Curve
MDF12N50B (TO-220F)

Physical Dimensions

3 Leads, TO-220

Dimensions are in millimeters unless otherwise specified

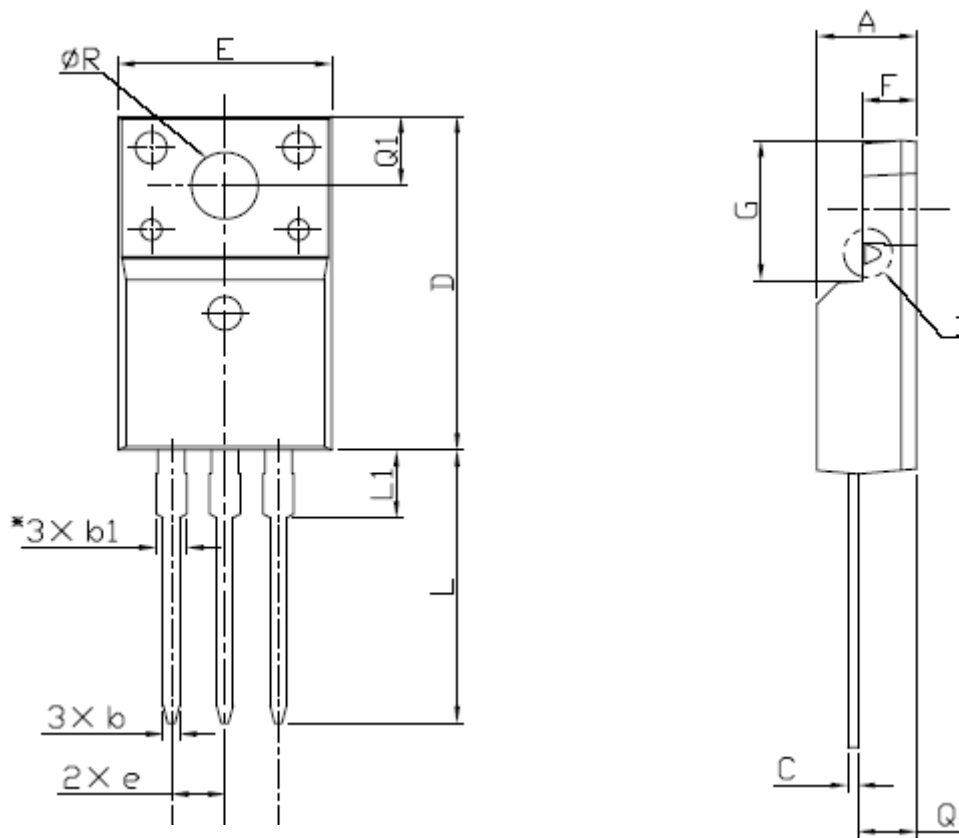


Symbol	Min	Nom	Max
A	3.56		4.83
A1	0.50		1.40
A2	2.03		2.92
b	0.38	0.69	1.02
b2	1.14	1.45	1.78
c	0.36		0.61
D	14.22		16.51
e	2.54 TYP		
E	9.65		10.67
H1	5.84		6.86
L	12.70		14.73
L1			6.35
Φ P	3.53		4.09
Q	2.54		3.43

Physical Dimension

3 Leads, TO-220F

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	4.50		4.93
b	0.63		0.91
b1	1.15		1.47
C	0.33		0.63
D	15.47		16.13
E	9.60		10.71
e		2.54	
F	2.34		2.84
G	6.48		6.90
L	12.24		13.72
L1	2.79		3.67
Q	2.52		2.96
Q1	3.10		3.50
ØR	3.00		3.55

Worldwide Sales Support Locations

U.S.A

Sunnyvale Office

787 N. Mary Ave. Sunnyvale
CA 94085 U.S.A
Tel : 1-408-636-5200
Fax : 1-408-213-2450
E-Mail : usasales@magnachip.com

U.K

Knyvett House The Causeway,
Staines Middx, TW18 3BA, U.K.
Tel : +44 (0) 1784-895-000
Fax : +44 (0) 1784-895-115
E-Mail : uksales@magnachip.com

Japan

Osaka Office

3F, Shin-Osaka MT-2 Bldg 3-5-36
Miyahara Yodogawa-Ku
Osaka, 532-0003 Japan
Tel : 81-6-6394-9160
Fax : 81-6-6394-9150
E-Mail : osakasales@magnachip.com

Taiwan R.O.C

2F, No.61, Chowize Street, Nei Hu
Taipei, 114 Taiwan R.O.C
Tel : 886-2-2657-7898
Fax : 886-2-2657-8751
E-Mail : taiwansales@magnachip.com

China

Hong Kong Office

Suite 1024, Ocean Centre 5 Canton Road,
Tsim Sha Tsui Kowloon, Hong Kong
Tel : 852-2828-9700
Fax : 852-2802-8183
E-Mail : chinasales@magnachip.com

Shenzhen Office

Room 2003B, 20/F
International Chamber of Commerce Tower
Fuhua Road3 CBD, Futian District, China
Tel : 86-755-8831-5561
Fax : 86-755-8831-5565
E-Mail : chinasales@magnachip.com

Shanghai Office

Room E, 8/F, Liaoshen International Building 1068
Wuzhong Road, (C) 201103
Shanghai, China
Tel : 86-21-6405-1521
Fax : 86-21-6505-1523
E-Mail : chinasales@magnachip.com

Korea

891, Daechi-Dong, Kangnam-Gu
Seoul, 135-738 Korea
Tel : 82-2-6903-3451
Fax : 82-2-6903-3668 ~9
Email : koreasales@magnachip.com

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